



37 CFR 1.98(A)(1) Reference Citation

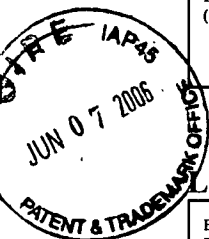
NEIFELD IP LAW REFERENCE FORM LIST OF REFERENCES CITED BY THE APPLICANT (Rev: 5/14/2003)	NEIFELD REF: OSEMDB1SUPCTUS	APPLICATION NO: 10/579,537
	FIRST NAMED INVENTOR: Braddock	
	FILING DATE: 5/16/2006	GROUP ART UNIT: Unknown

LISTING OF UNITED STATES PATENTS

EXAMINER INITIALS	REFERENCE NUMBER (U SERIES)	PATENT NUMBER	ISSUE DATE	NAME OF PATENTEE OR APPLICANT	PAGE/LINE AND FIGURE/ELEMENT OF RELEVANT MATERIAL AND/OR IDENTIFICATION OF PRIORITY APPLICATION IN WHICH REFERENCE IS CITED
	U-001	3,950,273	4-1976	Jones	
	U-002	4,404,265	9-1983	Manasevit	
	U-003	4,410,902	10-1983	Malik	
	U-004	4,416,952	11-1983	Nishizawa et al.	
	U-005	4,561,915	12-1985	Mito	
	U-006	4,624,901	11-1986	Glass	
	U-007	4,671,777	6-1987	van Esdonk et al.	
	U-008	4,685,193	8-1987	Faria et al.	
	U-009	4,745,082	5-1988	Kwok	
	U-010	4,802,180	1-1989	Brandle, Jr. et al.	
	U-011	4,843,450	6-1989	Kirchner et al.	
	U-012	4,859,253	8-1989	Buchanan et al.	
	U-013	4,935,789	6-1990	Calviello	
	U-014	4,970,060	11-1990	Belt et al.	
	U-015	5,055,445	10-1991	Belt et al.	
	U-016	5,124,762	6-1992	Childs et al.	
	U-017	5,170,407	12-1992	Schubert et al.	
	U-018	5,270,798	12-1993	Pao et al.	
	U-019	5,323,053	6-1994	Luryi et al.	
	U-020	5,386,137	1-1995	Dell et al.	
	U-021	5,425,043	6-1995	Holonyak et al.	
	U-022	5,451,548	9-1995	Hunt et al.	
	U-023	5,491,712	2-1996	Lin et al.	
	U-024	5,550,089	8-1996	Dutta et al.	
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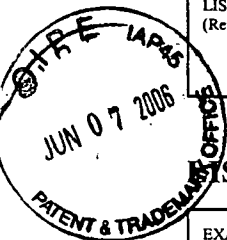


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	U-025	5,597,768	1-1997	Passlack et al.	
	U-026	5,640,751	6-1997	Faria	
	U-027	5,665,658	9-1997	Passlack	
	U-028	5,693,565	12-1997	Camilletti et al.	
	U-029	5,729,563	3-1998	Wang et al.	
	U-030	5,767,388	6-1998	Fleisher et al.	
	U-031	5,805,624	9-1998	Yang et al.	
	U-032	5,821,171	10-1998	Hong et al.	
	U-033	5,838,708	11-1998	Lin et al.	
	U-034	5,896,408	4-1999	Corzine et al.	
	U-035	5,930,611	7-1999	Okamoto	
	U-036	5,945,718	8-1999	Passlack et al.	
	U-037	5,953,362	9-1999	Pamulapati et al.	
	U-038	6,006,582	12-1999	Bhandari et al.	
	U-039	6,028,693	2-2000	Fork et al.	
	U-040	6,030,453	2-2000	Passlack et al.	
	U-041	6,045,611	4-2000	Ishii et al.	
	U-042	6,069,908	5-2000	Yuen et al.	
	U-043	6,071,780	6-2000	Okamoto et al.	
	U-044	6,094,295	7-2000	Passlack et al.	
	U-045	6,114,079	9-2000	Christian et al.	
	U-046	6,150,677	11-2000	Tanaka et al.	
	U-047	6,207,976	3-2001	Takahashi et al.	
	U-048	6,252,896	6-2001	Tan et al.	
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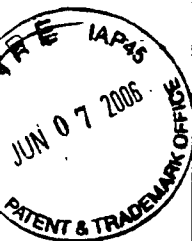
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	U-049	6,313,511	11-2001	Noguchi	
	U-050	6,347,049	2-2002	Childress et al.	
	U-051	6,445,015	9-2002	Braddock	
	U-052	6,451,711	9-2002	Braddock, IV	
	U-053	6,573,528	6-2003	Braddock	
	U-054	6,670,651	12-2003	Braddock	
	U-055	4,916,498	4-1990	Berenz	
	U-056	6,121,153	9-2000	Kikkawa	
	U-057	6,347,104	2-2002	Dijaili et al.	
	U-058	5,900,653	5-1999	Suzuki et al.	
	U-059	5,739,557	4-1998	O'Neil et al.	
	U-060	5,912,498	6-1999	Hobson et al.	
	U-061	2,993,814	7/25/1961	Epprecht et al.	
	U-062	4,239,955	12/16/1980	Cho	
	U-063	4,553,022	11/12/1985	Columbo	
	U-064	4,810,526	3/7/1989	Ito et al.	
	U-065	6,162,300	12/19/2000	Bicht	
	U-066	6,936,900	8/30,2005	Braddock, IV	
	U-067	6,989,556	1/24/2006	Braddock, IV	

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LISTING OF UNITED STATES PUBLISHED APPLICATIONS

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 PATENT & TRADEMARK OFFICE

TESTING OF FOREIGN AND INTERNATIONAL PATENT DOCUMENTS

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /J.K./

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LISTING OF NON PATENT LITERATURE

EXAMINER INITIALS	REFERENCE NUMBER (O Series)	PUBLICATION DATE	INCLUDE IN SEQUENCE: Name of first author (in CAPITAL LETTERS), Title in quotation marks, name of publication, date or publication, page numbers, publisher, city of publication, and country of publication	ENGLISH LANGUAGE TRANSLATION ATTACHED? (YES OR NO) AND/OR OR IDENTIFICATION OF PRIORITY APPLICATION IN WHICH REFERENCE IS CITED
	O-001	1994	"1995-1996 Alfa AESAR Catalog," 1994, page 1244, Johnson Matthey Catalog Company, Inc., Ward Hill, MA, US.	
	O-002	6-2001	VURGAFTMAN et al., "Band Parameters for III-V Semiconductors and Their Alloys," J. Appl. Phys. PP 5816-5875 (June 1, 2001).	
	O-003	2003	"Gallium Oxide on Gallium Arsenide: Atomic Structure, Materials, and Devices," Chapter 12, either published or scheduled for publication in "Gallium Oxide on Gallium Arsenide: Atomic Structure, Materials, and Devices," in III-IV Semiconductor Heterostructures: Physics and Devices, edited by W.Z. Cai, Transworld Research Publisher, Kerala, India (2003).	
	O-004	7-1996	PASSLACK et al., "Thermodynamic and photochemical stability of low interface state density Ga ₂ O ₃ -GaAs structures fabricated by in-situ molecular beam epitaxy", Applied Physics Letters, Vol 69, No 3, pps 302-304, 15 July 1996.	
	O-005	6-1997	PASSLACK et al., " Recombination velocity at oxide-GaAs interfaces fabricated by in-situ molecular beam epitaxy", Applied Physics Letters, Volume 68, Number 25, pages 3605-3607, 17 June 1997.	
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	O-007	8-1997	UEDA et al., "Anisotropy of electrical and optical properties in B-Ga ₂ O ₃ single crystals", Applied Physics Letters, Volume 71, Number 7, Pages 933-935, 18 August 1997.	

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	O-008	6-1997	UEDA et al., "Synthesis and control of conductivity of ultraviolet transmitting B-Ga ₂ O ₃ single crystals", Applied Physics Letters, Volume 70, Number 26, pages 3561-3563, 30 June 1997.	
	O-009	2-2000	KHAN et al., "AlGa _N /Ga _N Metal Oxide Semiconductor Heterostructure Field Effect Transistor", IEEE Electron Device Letters, Volume 21, Number 2, pages 63-65, Feb. 2000.	
	O-010	3-2004	Takebe et al., "GaAs-MISFETs With Insulating Gate Films Formed by Direct Oxidation and by Oxinitridation fo Recessed GaAs Surfaces	
	O-011	1965	Becke et al., "Gallium Arsenide MOS Transistors," Solid-State Electronics, Pergamon Press 1965, Vol. 8, pp. 813-823.	
	O-012	1996	Passlack et al., "C-V and G-V Characterization of In-Situ Fabricated Ga ₂ O ₃ -GaAs Interfaces for Inversion/Accumulation Device and Surface Passivation Applications, Solid-State Electronics, Vol. 39, No. 8, pp. 1133-1136, 1996.	
	O-013	1996	Passlack et al., "GaAs Surface Passivation Using in-Situ Oxide Deposition," Applied Surface Science 104/105 (1996) 441-447.	
	O-014	June 1995	Passlack et al., "Infrared Microscopy Studies on High-Power InGaAs-GaAs-InGaP Lasers with Ga ₂ O ₃ Facet Coatings," IEEE Journal of Selected Topics in Quantum Electronics, Vol. 1, No. 2, June 1995, pp. 110-116.	
	O-015	12/15/1995	Passlack et al., "Capacitance-Voltage and Current-Voltage Characterization of Al _x Ga _{1-x} As-GaAs Structures," J. Appl. Phys. 78 (12), December 15, 1995, pp. 7091-7098.	
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	O-016	1997	Hong et al., "Novel Ga ₂ O ₃ (Gd ₂ O ₃) Passivation Techniques to Product Low Dit Oxide-GaAs Interfaces," Journal of Crystal Growth 175/176 (1997), pp. 422-427.	
	O-017	May 1996	Hong et al., "Low Interface State Density Oxide-GaAs Structures Fabricated by in Situ Molecular Beam Epitaxy," J. Vac. Sci. Technol. B 14(3), May/Jun 1996, pp. 2297-2300.	
	O-018	Feb 1997	Passlack et al., "Low Dit, Thermodynamically Stable Ga ₂ O ₃ -GaAs Interfaces: Fabrication, Characterization, and Modeling," IEEE Transactions on Electron Devices, Vol. 44, No. 2, February 1997.	
	O-019	12/21/2004	European Patent Office Supplementary European Search Report for Application Number EPO1956104.	
	O-020	6/15/2005	International Search Report for PCT/US04/38235.	
	O-021	10/26/2005	International Search Report for PCT/US04/38582.	
	O-022	10/29/2001	International Search Report for PCT/US01/24263.	
	O-023	4/4/2002	International Search Report for PCT/US01/25150.	
	O-024	12/20/2001	International Search Report for PCT/US01/25259.	
	O-025	1/16/2002	International Search Report for PCT/US01/25161.	

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